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another.

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4. (Amended) The semiconductor device according to claim 3, wherein each of said at least one adhesion layer has an etching rate which is essentially equivalent to an etching rate of said plurality of wiring lines.

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5. (Amended) The semiconductor device according to claim 4, wherein at least one of said at least one adhesion layer comprises tungsten.

Please add the following new claim 14, as follows:

14. (New) A semiconductor device comprising:

a multi-layer insulating layer, comprising:

a middle layer comprised of PAE (Poly Arylene Ether);

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an upper insulating layer and a lower insulating layer between which said middle layer is sandwiched, said upper and lower layers each comprised of HSQ (Hydrogen Silsesquioxane); and

an opening formed in a predetermined position in said PAE layer and said HSQ layers; and

a wiring line formed within said opening, said wiring line comprised of Cu having a concentration equal or higher than 10^{19} atoms/cm³.
